

Notice of References Cited	Application/Control No. 10/549,494		Applicant(s)/Patent Under Reexamination SASAKI ET AL.	
	Examiner MATTHEW J. SONG		Art Unit 1792	Page 1 of 1

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*	C	US-6,398,867 B1	06-2002	D'Evelyn et al.	117/11
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	V	Kawamura et al., "Synthesis of Bulk GaN single crystals using Na-Ca flux", Jpn. J. Appl. Phys. Vol 41 (2002). pp. L1440-L1442.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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